

AMENDMENTS TO THE SPECIFICATION

Please amend the title as follows:

Method for Manufacturing a Semiconductor Device Suitable for the Formation of a
Wiring Layer

Please amend the paragraph beginning at page 16, line 3 as follows:

Subsequently, as shown in Fig. 2F, by etching the SiO₂ film 8, the SiC film 7, and the SiO₂ film 6, ~~and the SiC film 5 (four-layer hard mask)~~ with the lower resin film 21 as a mask, the via hole pattern (second pattern) is formed on these films.

Please delete the following paragraph beginning at page 16, line 23.

The etching of SiC film 5 is performed using the plasma etching device, for example, under the condition of 30 sccm of CH₂F₂, 20 sccm of O₂, 50 sccm of Ar, 50 sccm of N₂, 2.67 Pa (20 mTorr) of pressure, and 200 W of RF source power.

Please amend the paragraph beginning at page 17, line 1 as follows:

As a result of these series of etching, the via hole pattern (second pattern) is formed on the SiC film 7, and the SiO₂ film 6, ~~and the SiC film 5.~~